

Oral presentation | CS Code-sharing session | 【CS.9】 Code-sharing Session of 13.7 & 15.6

[22p-E302-1~15]CS.9 Code-sharing Session of 13.7 &15.6

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Tue. Mar 22, 2022 1:45 PM - 6:30 PM E302 (E302)

△ : Presentation by Applicant for JSAP Young Scientists Presentation Award

▲ : English Presentation

▼ : Both of Above

No Mark : None of Above

2:15 PM - 2:45 PM

[22p-E302-2][The 43rd Best Review Paper Award Speech] Recent development of vertical GaN power devices

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Keywords:GaN, power device

This presentation reviews current status of vertical GaN power devices on GaN substrates, including our developed Schottky barrier diode (SBD) / trench MOSFET technology and examples of their circuit applications. Key remaining issues for the practical applications are also described.